



In the United States Patent and Trademark Office

Serial Number: 10/765,638

Appn. Filed: 2004, Jan. 27

Applicant(s): Alla Shukh

Appn. Title: Magnetic Tunnel Junction Memory Device

Examiner/GAU: _____

Mailed: 2004, Mar. 23

At: Edina, MN

Amendment A

Commissioner for Patents

Washington, District of Columbia 20231

Sir:

Prior to examination, please amend the above application as follows:

Specification:

Page 1, lines 16-22 delete and substitute the following:

- Cross-reference to Related Application

This application claims the benefit of the filing date of U.S. Provisional Patent Application Ser. No. 60/444,240 entitled "Magnetic Tunnel Junction Memory Cell with Perpendicular Magnetic Anisotropy in Free and Pinned Layers", filed Feb. 1, 2003. —

REMARKS

The above amendment is provided in response to the statutory requirement that applicant insert a reference to applicant's PPA.

Very respectfully,

Applicant(s):

Alllyn —

03-22-2004

Enc.: PTO-1449 & References

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